

	Type	L #	Hits	Search Text	DBS	Time Stamp
1	IS&R	L1	2	("6362033") .PN.	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/09 10:21
2	BRS	L2	7	("4198250" "4394182" "5053849" "5650343" "5741736" "6013570" "6140218") .PN.	US- PGPUB; USPAT; USOCR	2004/12/09 10:24
3	BRS	L3	0	("6362033") .URPN.	USPAT	2004/12/09 10:44
4	BRS	L4	2023	LDD or "lightly doped 3 drain"	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2004/12/09 10:44
5	BRS	L5	9084	tft or "thin film 2 transistor"	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2004/12/09 10:44
6	BRS	L6	3790	5 or lcd or "liquid 73 crystal display"	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2004/12/09 10:45

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7	BRS	L7	2933 61	implant\$6 or inplant\$6	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2004/12/09 10:45
8	BRS	L8	6252 38	P/R or resist or photoresist or photo- resist	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2004/12/09 10:46
9	BRS	L9	9019 5	8 near4 mask\$6	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2004/12/09 10:47
10	BRS	L11	9850 98	gate	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2004/12/09 10:48
11	BRS	L12	1068	4 same 7 same 9 same 11	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2004/12/09 10:50

	Type	L #	Hits	Search Text	DBs	Time Stamp
12	BRS	L13	242	12 and 6	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2004/12/09 10:51
13	BRS	L14	194	13 and ((@ad<"20020912") or (@rlad<"20020912"))	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2004/12/09 10:53
14	BRS	L15	1046	gate near8 undercut	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2004/12/09 10:54
15	BRS	L16	7	14 and 15	US- PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2004/12/09 10:54

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	0	photoresist and lateral adj etching and (tft or thin adj film adj transistor) and semiconductor adj energy adj laboratory	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/12/09 16:10
2	L2	6	(("5605857") or ("5985731") or ("6395650")) .PN.	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/12/09 16:10
3	L4	219	photoresist and etching and (tft or thin adj film adj transistor) and semiconductor adj energy adj laboratory.as. and ldd	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/12/09 16:11
4	L5	390	photoresist near8 ldd	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/12/09 16:12
5	L6	354	5 and (transistor or tft)	US- PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	2004/12/09 16:12

	L #	Hits	Search Text	DBs	Time Stamp
6	L7	317	6 and ((@ad<"20020912") or (@rlad<"20020912"))	US- PGPUB; USPAT; EPO; JPO; DERWENT; ; IBM_TDB	2004/12/09 17:52
7	L8	324	(438/163).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWENT; ; IBM_TDB	2004/12/09 17:52
8	L9	15	8 and "undercut"	US- PGPUB; USPAT; EPO; JPO; DERWENT; ; IBM_TDB	2004/12/09 17:52